

HiPerFET™ Power MOSFETs

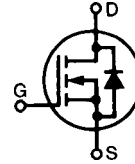
ISOPLUS247™

(Electrically Isolated Back Surface)

IXFR 30N50Q
IXFR 32N50Q

N-Channel Enhancement Mode
High dV/dt , Low t_{rr} , HDMOS™ Family

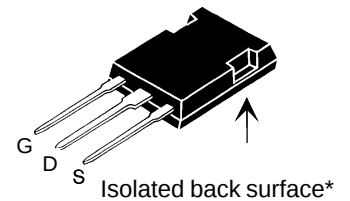
Preliminary data



V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	29 A	0.16 Ω
500 V	30 A	0.15 Ω
$t_{rr} \leq 250$ ns		

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	30N50 32N50	30 A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse width limited by T_{JM}	30N50 32N50	120 A
I_{AR}	$T_C = 25^\circ\text{C}$	30N50 32N50	30 A
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
E_{AR}	$T_C = 25^\circ\text{C}$	45	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2\text{ }\Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	310	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1$ minute leads-to-tab	2500	V~
Weight		6	g

ISOPLUS 247™
E 153432



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Low drain to tab capacitance (<50pF)
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2		4 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = I_T$ Notes 1, 2	30N50 32N50		0.16 Ω 0.15 Ω

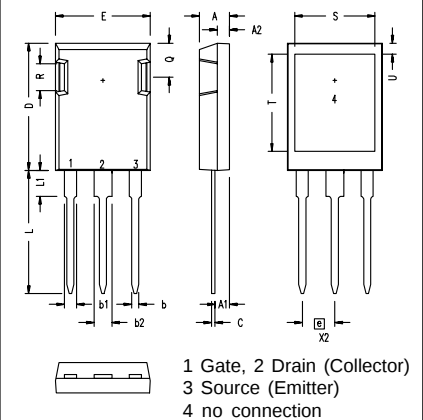
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$ Note 2	18	28	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3950	pF
C_{oss}			640	pF
C_{rss}			210	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),		35	ns
t_r			42	ns
$t_{d(off)}$			75	ns
t_f			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		150	nC
Q_{gs}			26	nC
Q_{gd}			85	nC
R_{thJC}			0.40	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			32 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			128 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S,$ $-di/dt = 100\text{ A/ms},$ $V_R = 100\text{ V}$			250 ns
Q_{RM}		0.75		μC
I_{RM}		7.5		A

- Note: 1. I_T test condition:
IXFR30N50: $I_T = 15\text{ A}$
IXFR32N50: $I_T = 16\text{ A}$
- Note: 2. Pulse test, $t \leq 300\ \mu\text{s}$,
duty cycle $d \leq 2\%$

ISOPLUS 247 (IXFR) OUTLINE



Dim.	Millimeter	Inches
	Min.	Max.
A	4.83	5.21
A ₁	2.29	2.54
A ₂	1.91	2.16
b	1.14	1.40
b ₁	1.91	2.13
b ₂	2.92	3.12
C	0.61	0.80
D	20.80	21.34
E	15.75	16.13
e	5.45 BSC	.215 BSC
L	19.81	20.32
L ₁	3.81	4.32
Q	5.59	6.20
R	4.32	4.83
S	13.21	13.72
T	15.75	16.26
U	1.65	3.03

Figure 1. Output Characteristics at 25°C

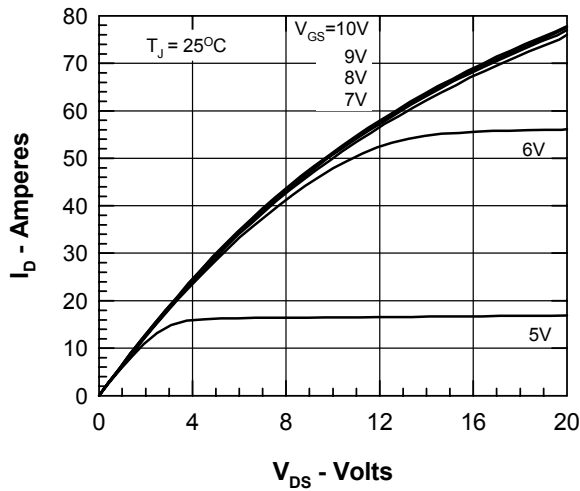


Figure 2. Output Characteristics at 125°C

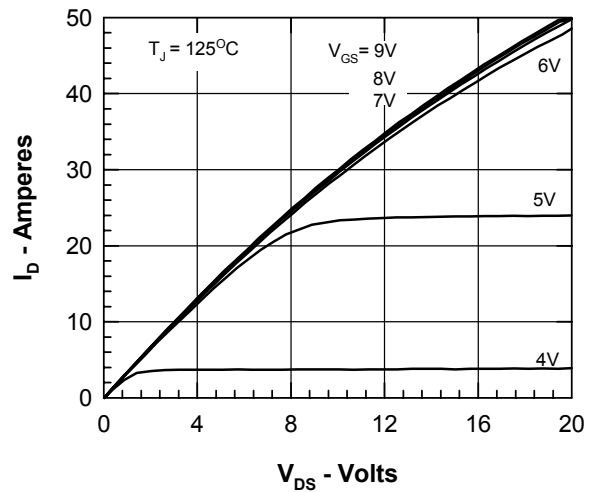
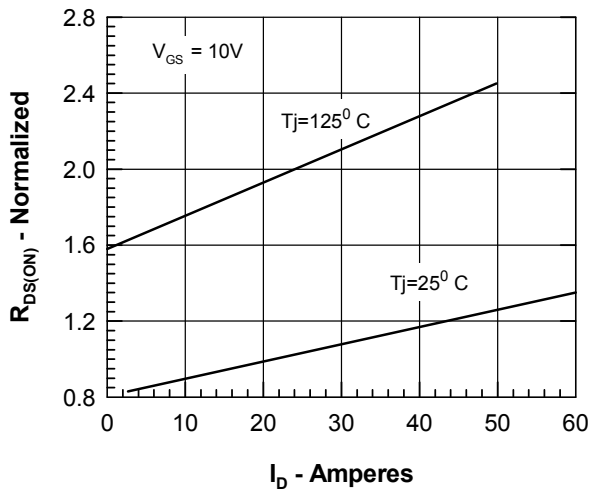
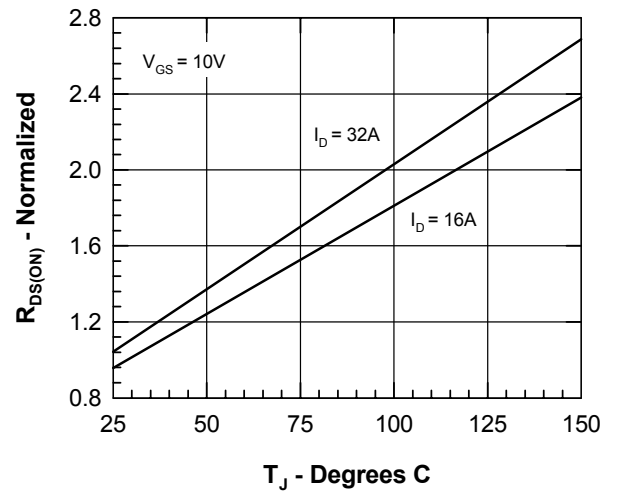

 Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

 Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_J


Figure 5. Drain Current vs. Case Temperature

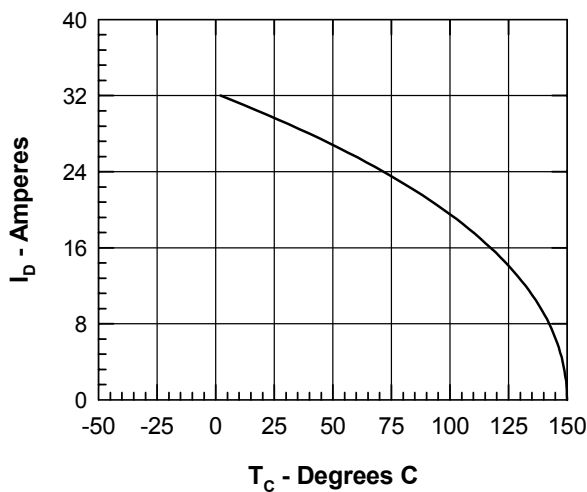


Figure 6. Admittance Curves

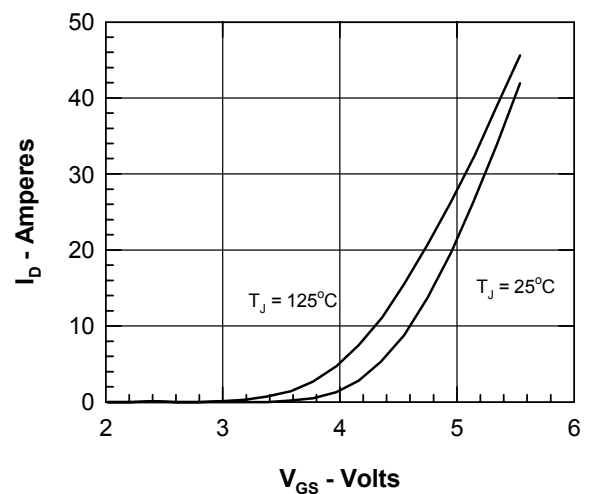


Figure 7. Gate Charge

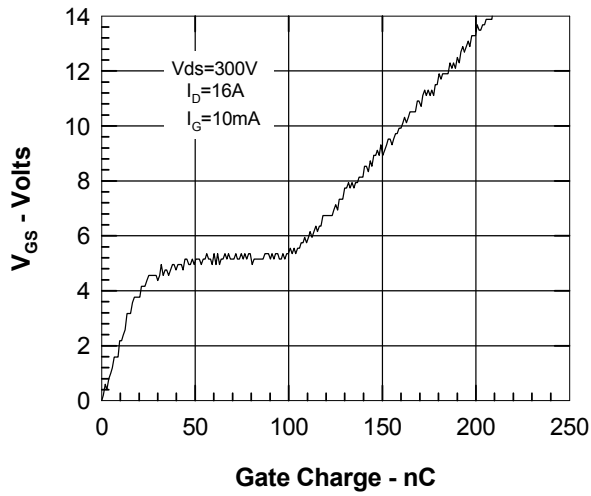


Figure 8. Capacitance Curves

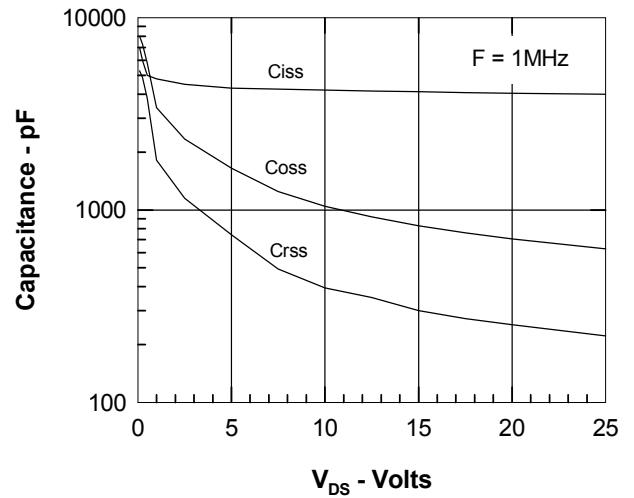


Figure 9. Forward Voltage Drop of the Intrinsic Diode

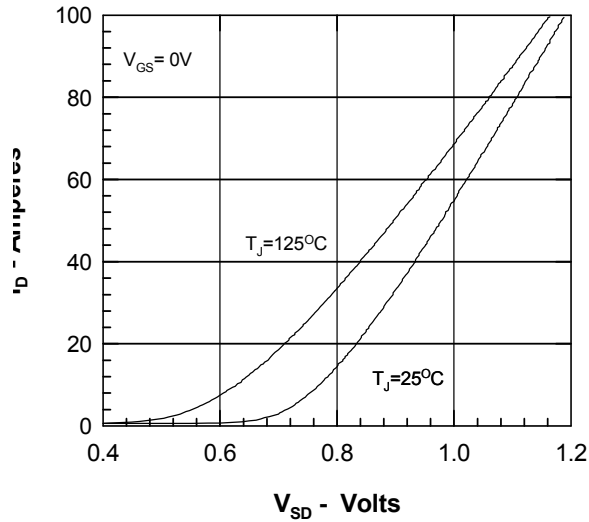


Figure 10. Transient Thermal Resistance

